

2N4400

MMBT4400





NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous 600		mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	ting and Storage Junction Temperature Range -55 to +150 °C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Units		Units
		2N4400	*MMBT4400	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

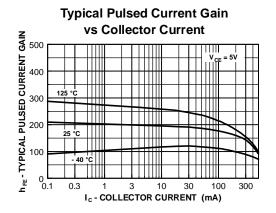
NPN General Purpose Amplifier (continued)

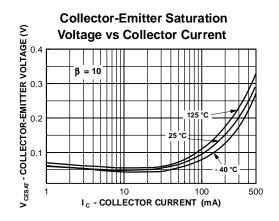
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	ARACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I _{BL}	Emitter Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	20		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	40	450	
		$V_{CE} = 1.0 \text{ V}, I_{C} = 150 \text{ mA}$ $V_{CE} = 2.0 \text{ V}, I_{C} = 500 \text{ mA}$	50 20	150	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	20	0.40	V
V CE(Sat)	Collector Entition Catalation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.75	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150 mA, I _B =15 mA	0.75	0.95	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.2	V
	1	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.2	V
SMALL S	SIGNAL CHARACTERISTICS				
	Output Capacitance	V _{CB} = 5.0 V, f = 140 kHz		6.5	V pF
SMALL S C _{ob} C _{ib}	Output Capacitance Input Capacitance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$			
C _{ob}	Output Capacitance	V _{CB} = 5.0 V, f = 140 kHz	2.0	6.5	pF
C _{ob} C _{ib} h _{fe}	Output Capacitance Input Capacitance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$	2.0	6.5	pF
C _{ob} C _{ib} h _{fe}	Output Capacitance Input Capacitance Small-Signal Current Gain	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	_	6.5	pF
C _{ob} C _{ib} h _{fe} h _{fe}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$	20	6.5 30 250	pF pF
C _{ob} C _{ib} h _{fe} h _{ie} h _{re}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$	20	6.5 30 250 7.5	pF pF
C _{ob}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF KΩ x 10 ⁻⁴
Cob Cib hfe hfe hie hre hoe	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF KΩ x 10 ⁻⁴
C _{ob} C _{ib} h _{fe} h _{fe} h _{ie} h _{re} h _{oe}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF KΩ x 10 ⁻⁴
Cob Cib hfe hfe hie hre hoe	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$	20 0.5 0.1	6.5 30 250 7.5 8.0 30	pF pF KΩ x 10 ⁻⁴ μmhos
C _{ob} C _{ib} h _{fe} h _{fe} h _{ie} h _{re} h _{oe}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance ING CHARACTERISTICS Delay Time	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$ $V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$	20 0.5 0.1	6.5 30 250 7.5 8.0 30	pF pF KΩ x 10 ⁻⁴ μmhos

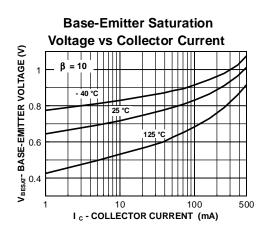
^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

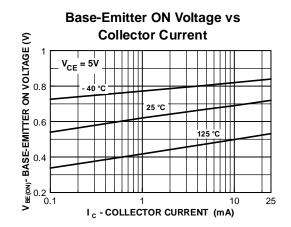
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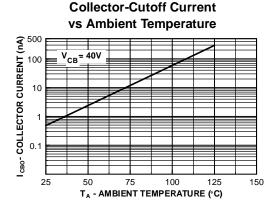
Typical Characteristics

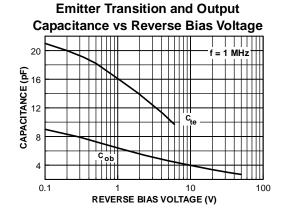








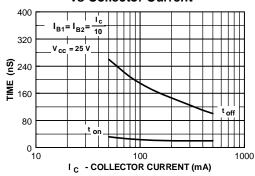




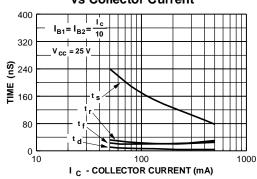
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Typical Characteristics (continued)

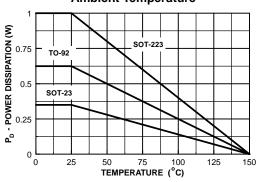
Turn On and Turn Off Times vs Collector Current



Switching Times vs Collector Current

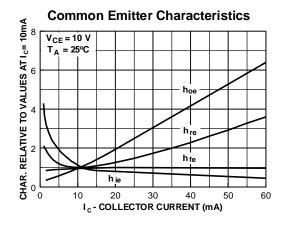


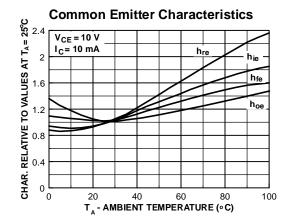
Power Dissipation vs Ambient Temperature

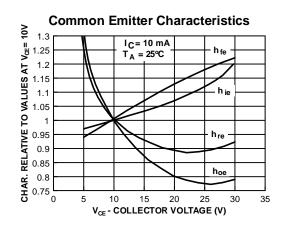


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Typical Common Emitter Characteristics (f = 1.0kHz)







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Test Circuits

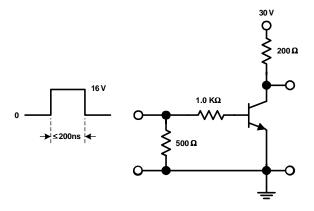


FIGURE 1: Saturated Turn-On Switching Timer

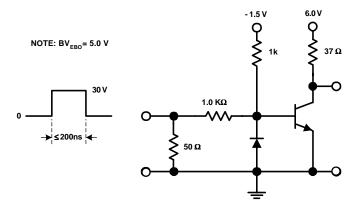


FIGURE 2: Saturated Turn-Off Switching Time

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